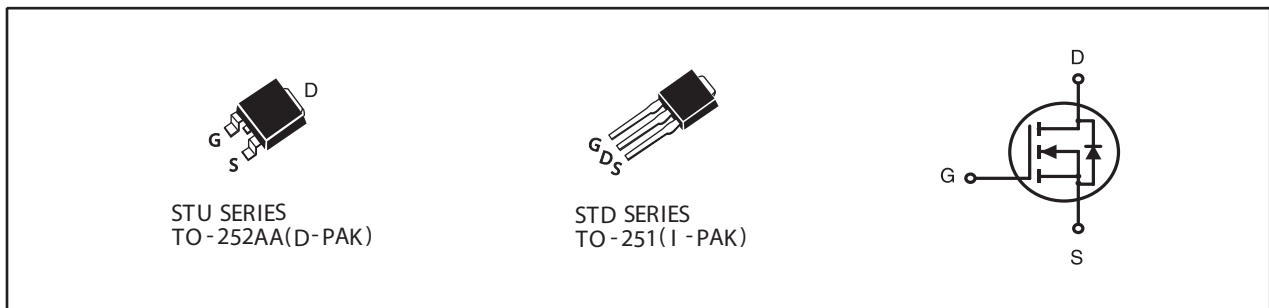


**N-Channel Logic Level Enhancement Mode Field Effect Transistor****PRODUCT SUMMARY**

V _{DSS}	I _D	R _{DS(ON)} (mΩ) Typ
200V	15A	190 @ V _{GS} =10V

FEATURES

- Super high dense cell design for low R_{DS(ON)}.
- Rugged and reliable.
- TO-252 and TO-251 Package.

**ABSOLUTE MAXIMUM RATINGS (T_C=25°C unless otherwise noted)**

Symbol	Parameter	Limit	Units
V _{DS}	Drain-Source Voltage	200	V
V _{GS}	Gate-Source Voltage	±20	V
I _D	Drain Current-Continuous ^{a e}	T _C =25°C	15
		T _C =70°C	12
I _{DM}	-Pulsed ^b	44	A
E _{AS}	Single Pulse Avalanche Energy ^d	64	mJ
P _D	Maximum Power Dissipation	T _C =25°C	78
		T _C =70°C	50
T _J , T _{STG}	Operating Junction and Storage Temperature Range	-55 to 150	°C

THERMAL CHARACTERISTICS

R _{θ JC}	Thermal Resistance, Junction-to-Case	1.6	°C/W
R _{θ JA}	Thermal Resistance, Junction-to-Ambient	50	°C/W

STU15N20

STD15N20

Ver 1.0

ELECTRICAL CHARACTERISTICS (T_C=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =10mA	200			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =160V , V _{GS} =0V			1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±20V , V _{DS} =0V			±100	nA
ON CHARACTERISTICS						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1	2	3	V
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =10V , I _D =7.5A		190	235	m ohm
g _{FS}	Forward Transconductance	V _{DS} =10V , I _D =7.5A		8		S
DYNAMIC CHARACTERISTICS ^c						
C _{ISS}	Input Capacitance	V _{DS} =25V, V _{GS} =0V f=1.0MHz		1615		pF
C _{OSS}	Output Capacitance			85		pF
C _{RSS}	Reverse Transfer Capacitance			64		pF
SWITCHING CHARACTERISTICS ^c						
t _{D(ON)}	Turn-On Delay Time	V _{DD} =100V I _D =1A		35		ns
t _r	Rise Time			31		ns
t _{D(OFF)}	Turn-Off Delay Time	V _{GS} =10V R _{GEN} = 6 ohm		54		ns
t _f	Fall Time			16		ns
Q _g	Total Gate Charge	V _{DS} =100V, I _D =1A, V _{GS} =10V		21.4		nC
Q _{gs}	Gate-Source Charge	V _{DS} =100V, I _D =1A, V _{GS} =10V		2.7		nC
Q _{gd}	Gate-Drain Charge			7.2		nC
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
V _{SD}	Diode Forward Voltage	V _{GS} =0V, I _S =5A		0.81	1.3	V
Notes						
<p>a.Surface Mounted on FR4 Board, t ≤ 10sec.</p> <p>b.Pulse Test:Pulse Width ≤ 300us, Duty Cycle ≤ 2%.</p> <p>c.Guaranteed by design, not subject to production testing.</p> <p>d.Starting T_J=25°C, L=0.5mH, V_{DD} = 50V.(See Figure13)</p> <p>e.Drain current limited by maximum junction temperature.</p>						

Oct,29,2013

STU15N20 STD15N20

Ver 1.0

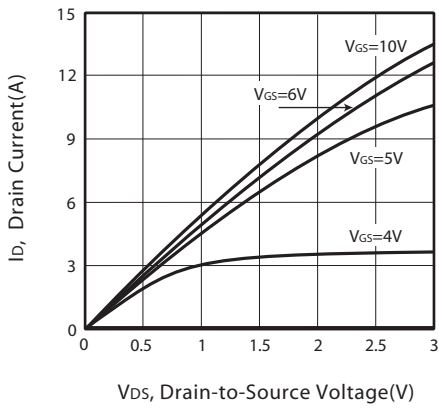


Figure 1. Output Characteristics

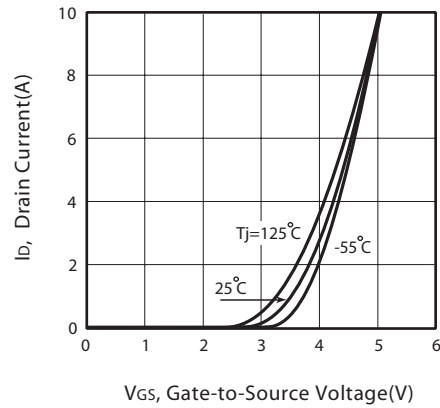


Figure 2. Transfer Characteristics

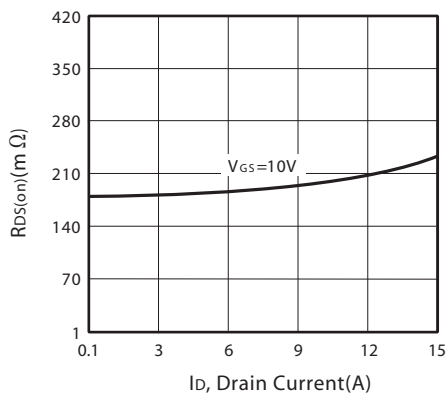


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

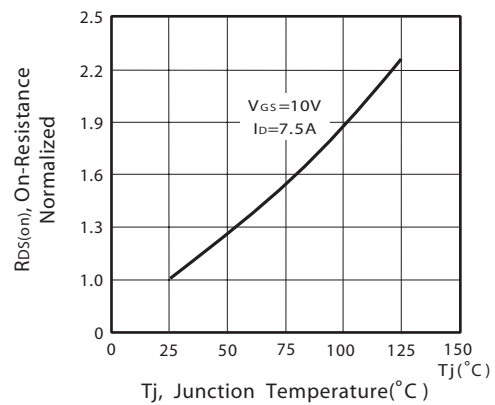


Figure 4. On-Resistance Variation with Drain Current and Temperature

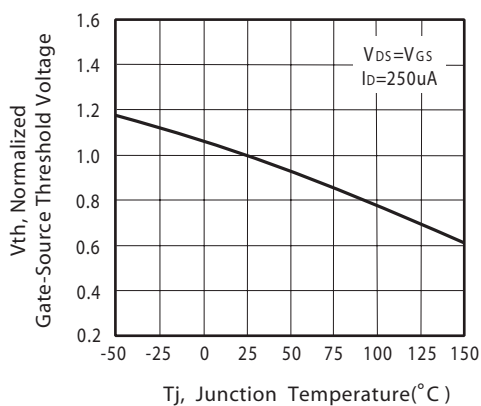


Figure 5. Gate Threshold Variation with Temperature

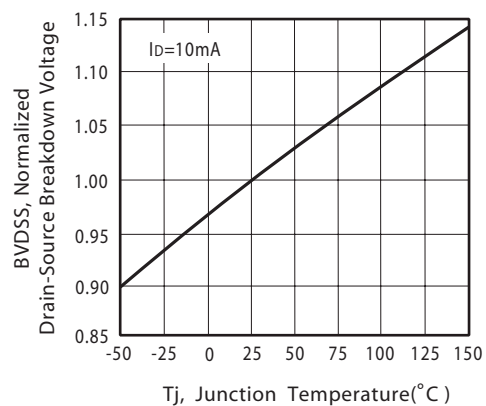


Figure 6. Breakdown Voltage Variation with Temperature

Oct,29,2013

STU15N20

STD15N20

Ver 1.0

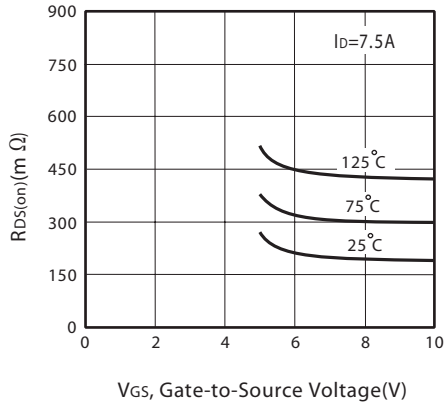


Figure 7. On-Resistance vs. Gate-Source Voltage

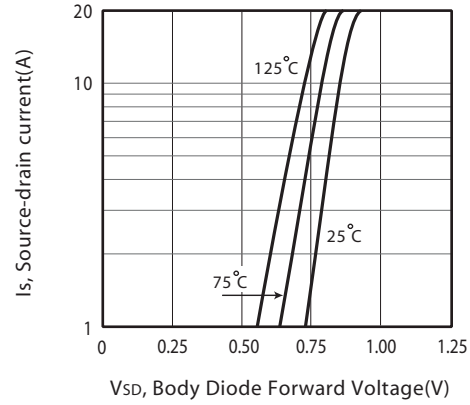


Figure 8. Body Diode Forward Voltage Variation with Source Current

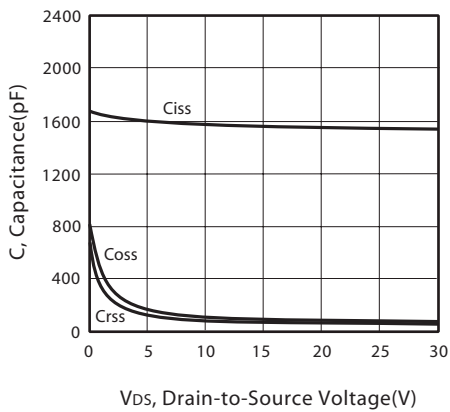


Figure 9. Capacitance

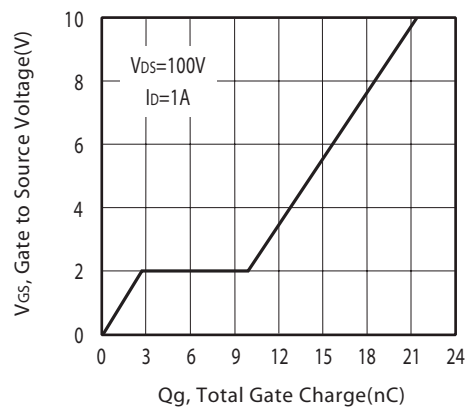


Figure 10. Gate Charge

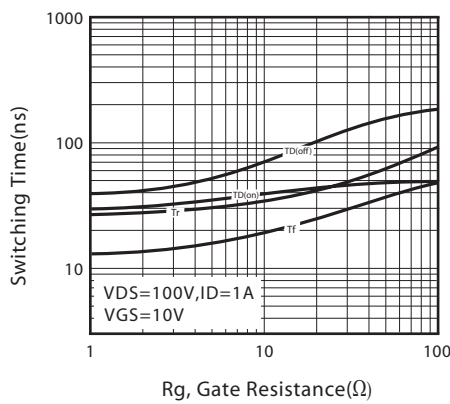


Figure 11. switching characteristics

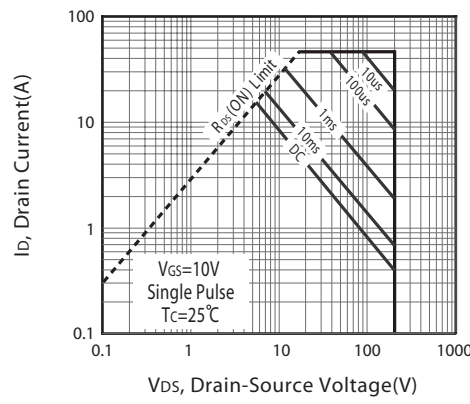
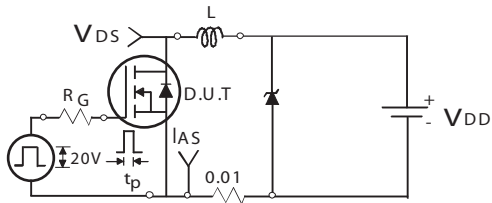


Figure 12. Maximum Safe Operating Area

Oct,29,2013

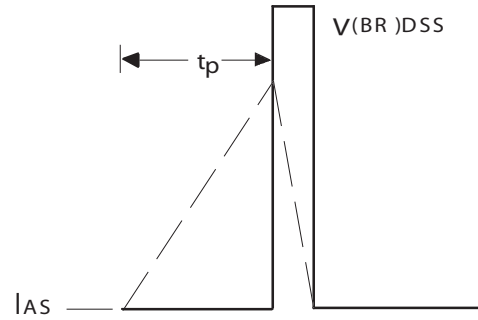
STU15N20 STD15N20

Ver 1.0



Unclamped Inductive Test Circuit

Figure 13a.



Unclamped Inductive Waveforms

Figure 13b.

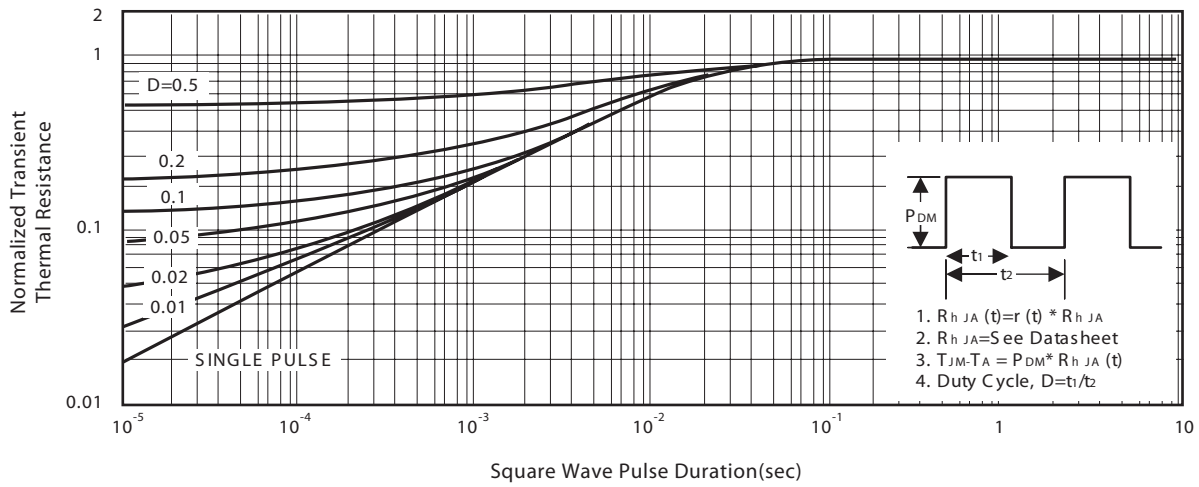


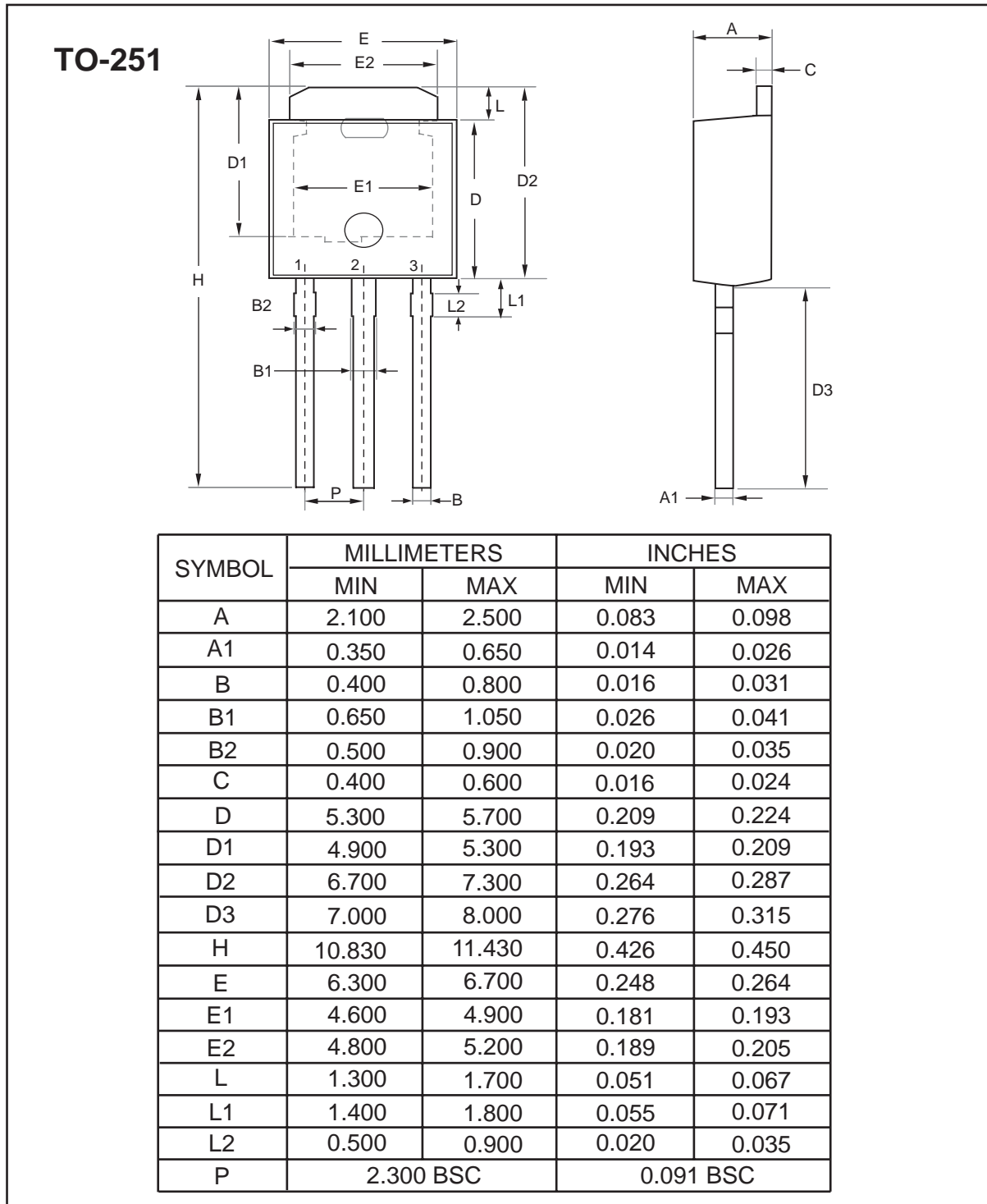
Figure 14. Normalized Thermal Transient Impedance Curve

Oct,29,2013

STU15N20 STD15N20

Ver 1.0

PACKAGE OUTLINE DIMENSIONS

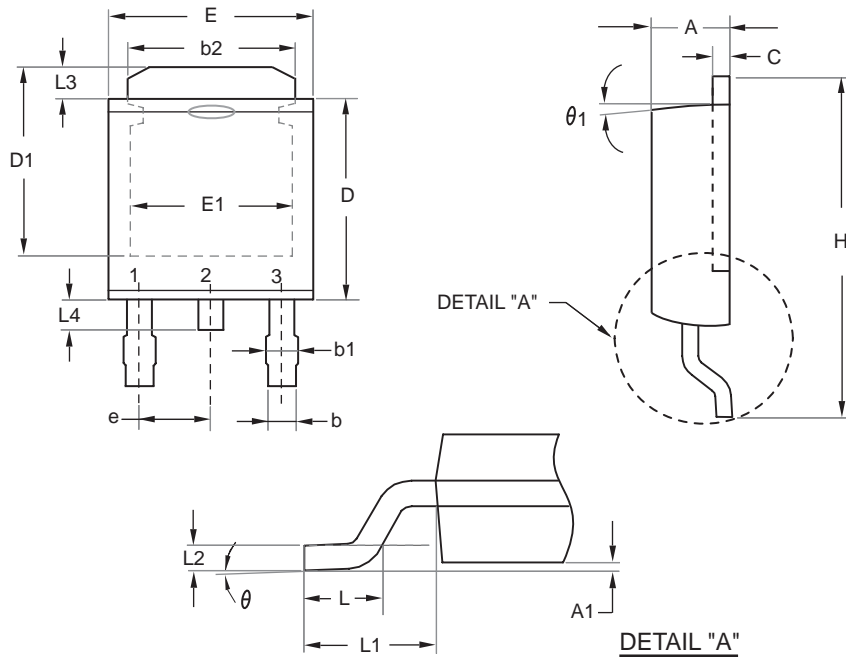


Oct,29,2013

STU15N20 STD15N20

Ver 1.0

TO-252



SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.100	2.500	0.083	0.098
A1	0.000	0.200	0.000	0.008
b	0.400	0.889	0.016	0.035
b1	0.770	1.140	0.030	0.045
b2	4.800	5.460	0.189	0.215
C	0.400	0.600	0.016	0.024
D	5.300	6.223	0.209	0.245
D1	4.900	5.515	0.193	0.217
E	6.300	6.731	0.248	0.265
E1	4.400	5.004	0.173	0.197
e	2.290 REF		0.090 BSC	
H	8.900	10.400	0.350	0.409
L	1.397	1.770	0.055	0.070
L1	2.743 REF.		0.108 REF.	
L2	0.508 REF.		0.020 REF.	
L3	0.890	1.700	0.035	0.067
L4	0.500	1.100	0.020	0.043
theta	0°	10°	0°	10°
theta1	7° REF.		7° REF.	

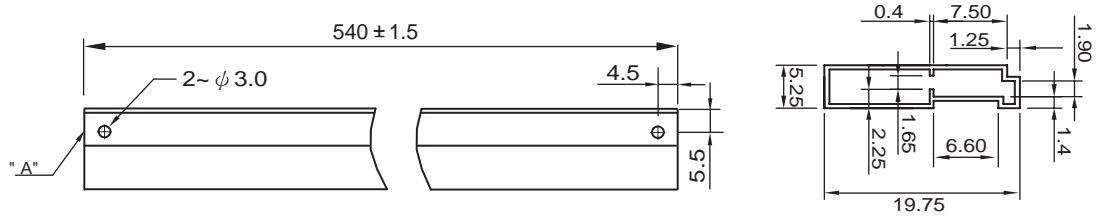
Oct,29,2013

STU15N20 STD15N20

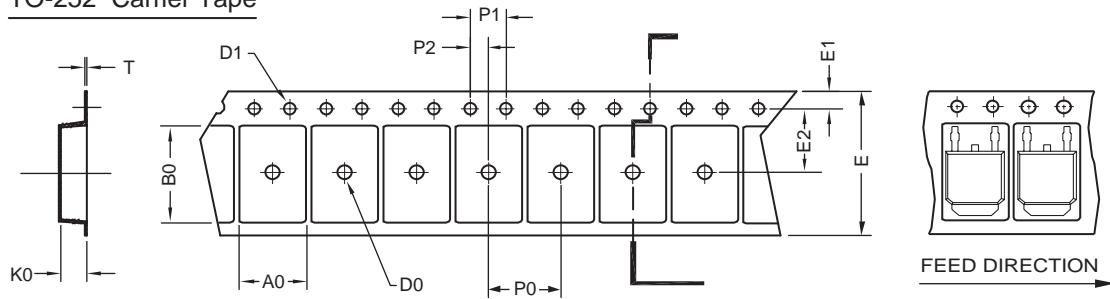
Ver 1.0

TO-251 Tube/TO-252 Tape and Reel Data

TO-251 Tube



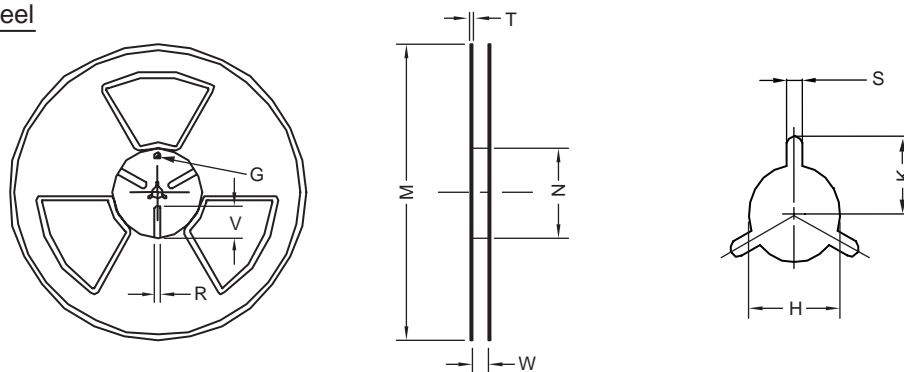
TO-252 Carrier Tape



UNIT:mm

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
TO-252 (16 mm)	6.96 ±0.1	10.49 ±0.1	2.79 ±0.1	φ 2	φ 1.5 +0.1 - 0	16.0 ±0.3	1.75 ±0.1	7.5 ±0.15	8.0 ±0.1	4.0 ±0.1	2.0 ±0.15	0.3 ±0.05

TO-252 Reel



UNIT:mm

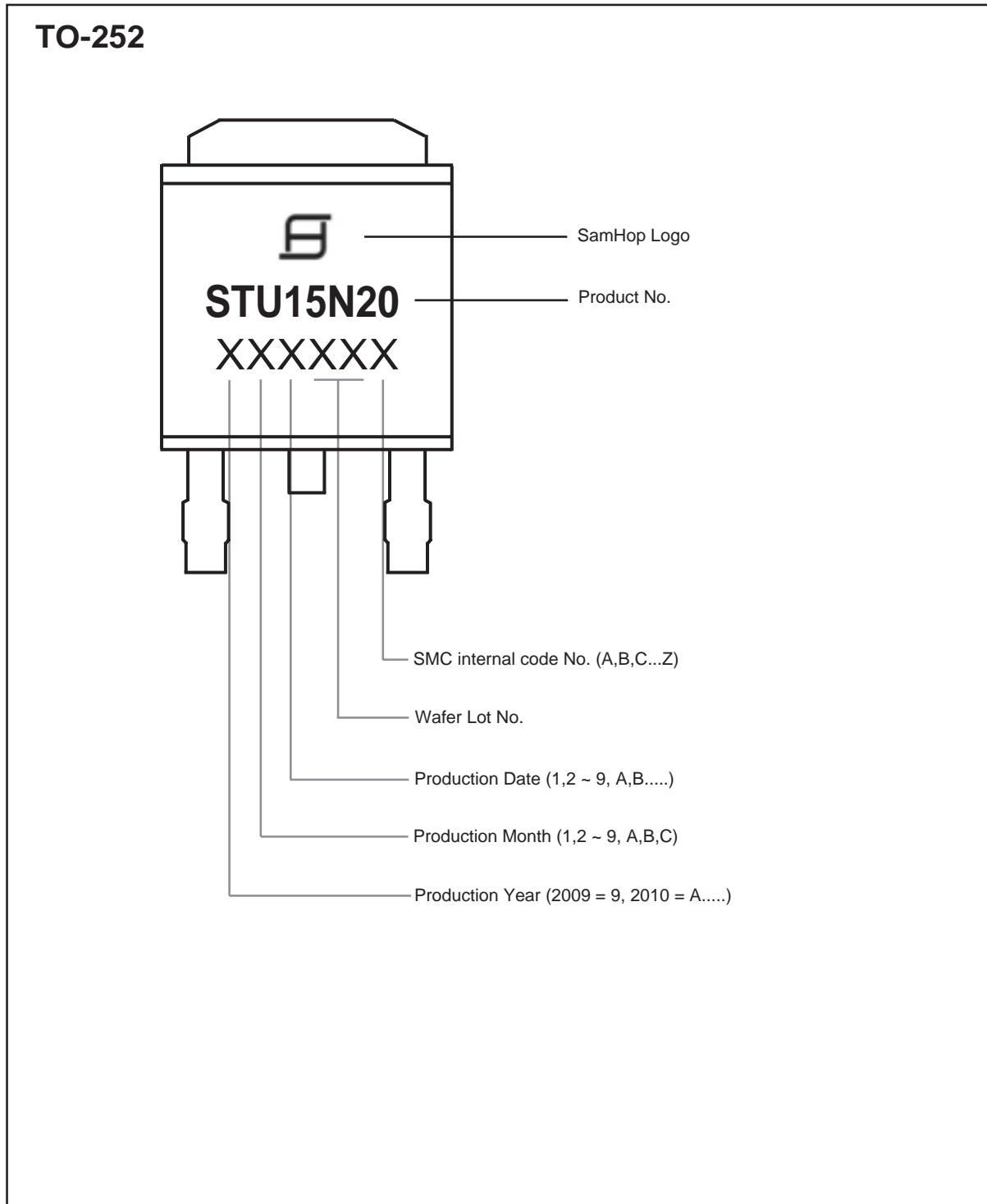
TAPE SIZE	REEL SIZE	M	N	W	T	H	K	S	G	R	V
16 mm	φ 330	φ 330 ± 0.5	φ 97 ± 1.0	17.0 + 1.5 - 0	2.2	φ 13.0 + 0.5 - 0.2	10.6	2.0 ±0.5	---	---	---

Oct,29,2013

STU15N20 STD15N20

Ver 1.0

TOP MARKING DEFINITION



Oct,29,2013

STU15N20 STD15N20

TOP MARKING DEFINITION

